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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	10/720,094
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				First Named Inventor	Yasunori BITO
				Art Unit	2826
				Examiner Name	Thomas L. DICKEY
Sheet	1	of	1	Attorney Docket Number	Q78644

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
TB		US 2001/0019131	A1	09-06-2001	Kato et al.
		US			
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FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)			
TB		EP	0940855	A2	09-08-1999	NEC Corporation	

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁶
TB		K. Nishii et al.; "High Current/gm Self-Aligned PJ-HFET of Completely Enhancement-Mode Operation"; Extended Abstracts of the International Conference on Solid State Devices and Materials; Japan Society of Applied Physics, Tokyo, Japan; September 1998; pages 396-397.	
TB		Y. Bito et al.; "64% Efficiency Enhancement-Mode Power Heterojunction FET for 3.5 V Li-ION Battery Operated Personal Digital Cellular Phones"; 1998 IEEE MTT-S International Microwave Symposium Digest; IMS '98; Progress Through Microwaves; Baltimore, MD, June 7-12, 1998; IEEE MTT-S International Microwave Symposium Digest, New York, NY: IEEE, US, Vol. 2, June 7, 1998; pages 439-442.	
TB		Y. Bito et al., Institute of Electrical and Electronics Engineers; "Enhancement-Mode Power Heterojunction FET utilizing Re-grown P+-GaAs Gate with Negligible Off-state Leakage Current"; 2003 IEEE MTT-S International Microwave Symposium Digest; (IMS 2003); Philadelphia, PA, June 8-13, 2003; IEEE MTT-S International Microwave Symposium, New York, NY: IEEE, US, Vol. 3 of 3, June 8, 2003; pages 703-706	

Examiner Signature		Date Considered	6/7/05
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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